

DATA SHEET



BC327

PNP general purpose transistor

Product specification
Supersedes data of 1997 Mar 10

1999 Apr 15

PNP general purpose transistor

BC327

FEATURES

- High current (max. 500 mA)
- Low voltage (max. 45 V).

APPLICATIONS

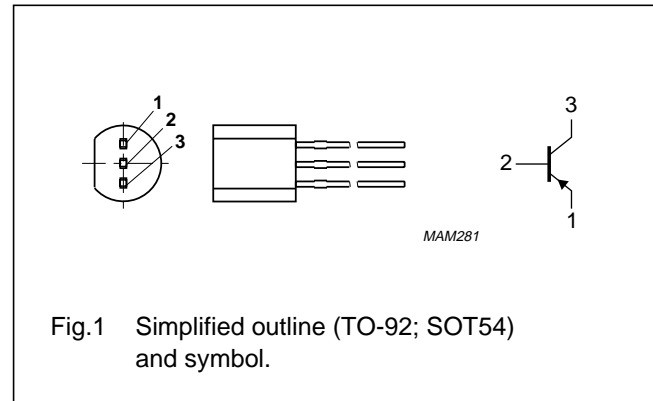
- General purpose switching and amplification, e.g. driver and output stages of audio amplifiers.

DESCRIPTION

PNP transistor in a TO-92; SOT54 plastic package.
NPN complement: BC337.

PINNING

PIN	DESCRIPTION
1	emitter
2	base
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–50	V
V_{CEO}	collector-emitter voltage	open base	–	–45	V
V_{EBO}	emitter-base voltage	open collector	–	–5	V
I_C	collector current (DC)		–	–500	mA
I_{CM}	peak collector current		–	–1	A
I_{BM}	peak base current		–	–200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; note 1	–	625	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

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BC327

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	0.2	K/mW

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

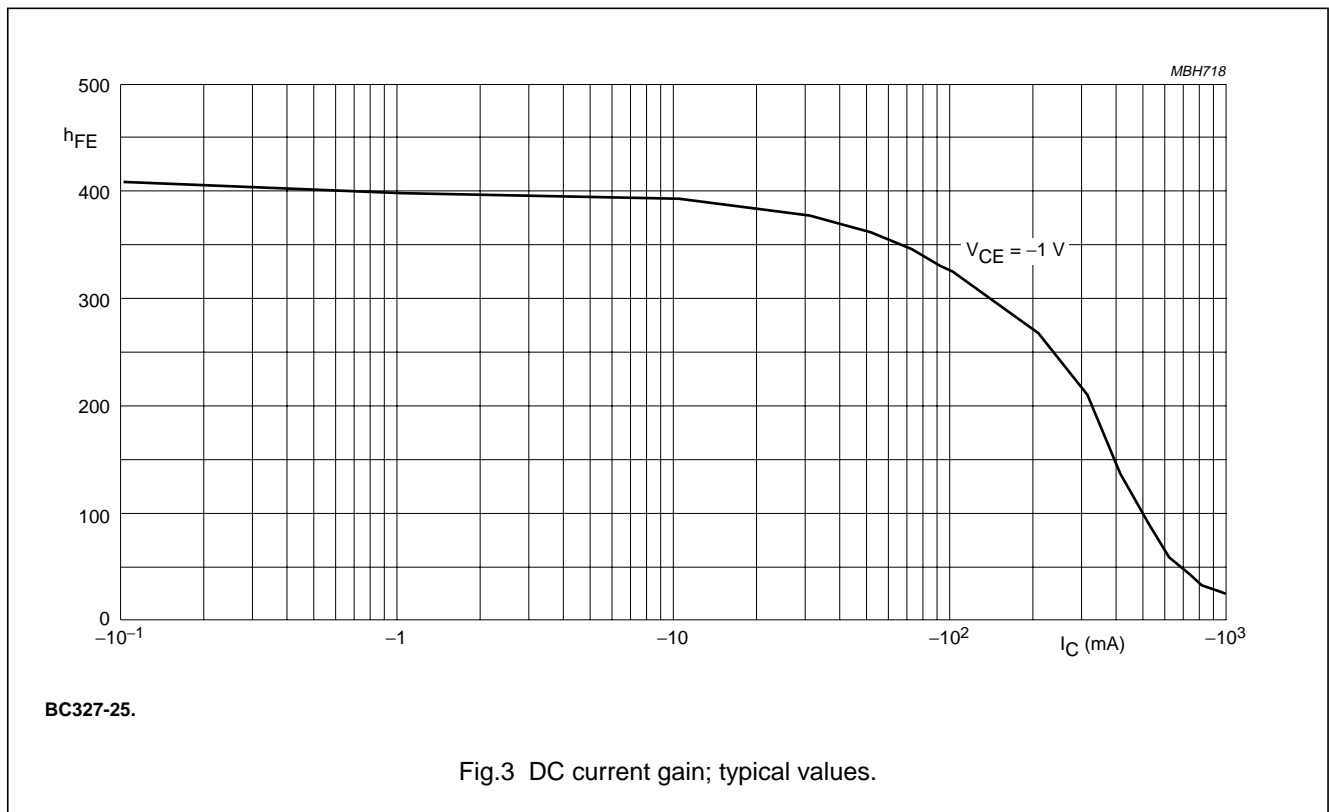
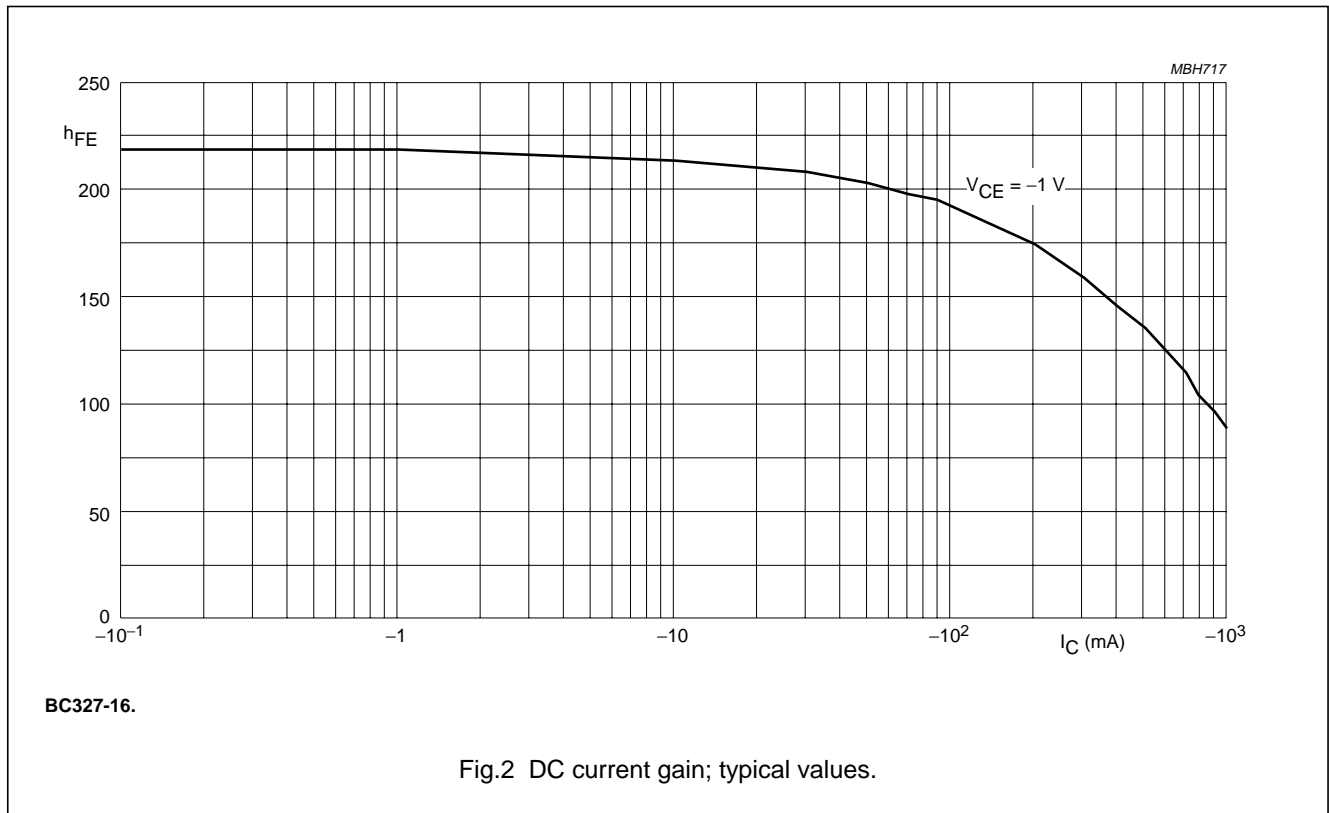
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = -20\text{ V}$	–	–	–100	nA
		$I_E = 0; V_{CB} = -20\text{ V}; T_j = 150\text{ °C}$	–	–	–5	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = -5\text{ V}$	–	–	–100	nA
h_{FE}	DC current gain BC327 BC327-16 BC327-25 BC327-40	$I_C = -100\text{ mA}; V_{CE} = -1\text{ V};$ see Figs 2, 3 and 4	100	–	600	
			100	–	250	
			160	–	400	
			250	–	600	
h_{FE}	DC current gain	$I_C = -500\text{ mA}; V_{CE} = -1\text{ V};$ see Figs 2, 3 and 4	40	–	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -500\text{ mA}; I_B = -50\text{ mA}$	–	–	–700	mV
V_{BE}	base-emitter voltage	$I_C = -500\text{ mA}; V_{CE} = -1\text{ V};$ note 1	–	–	–1.2	V
C_c	collector capacitance	$I_E = i_e = 0; V_{CB} = -10\text{ V}; f = 1\text{ MHz}$	–	10	–	pF
f_T	transition frequency	$I_C = -10\text{ mA}; V_{CE} = -5\text{ V};$ $f = 100\text{ MHz}$	80	–	–	MHz

Note

1. V_{BE} decreases by about -2 mV/K with increasing temperature.

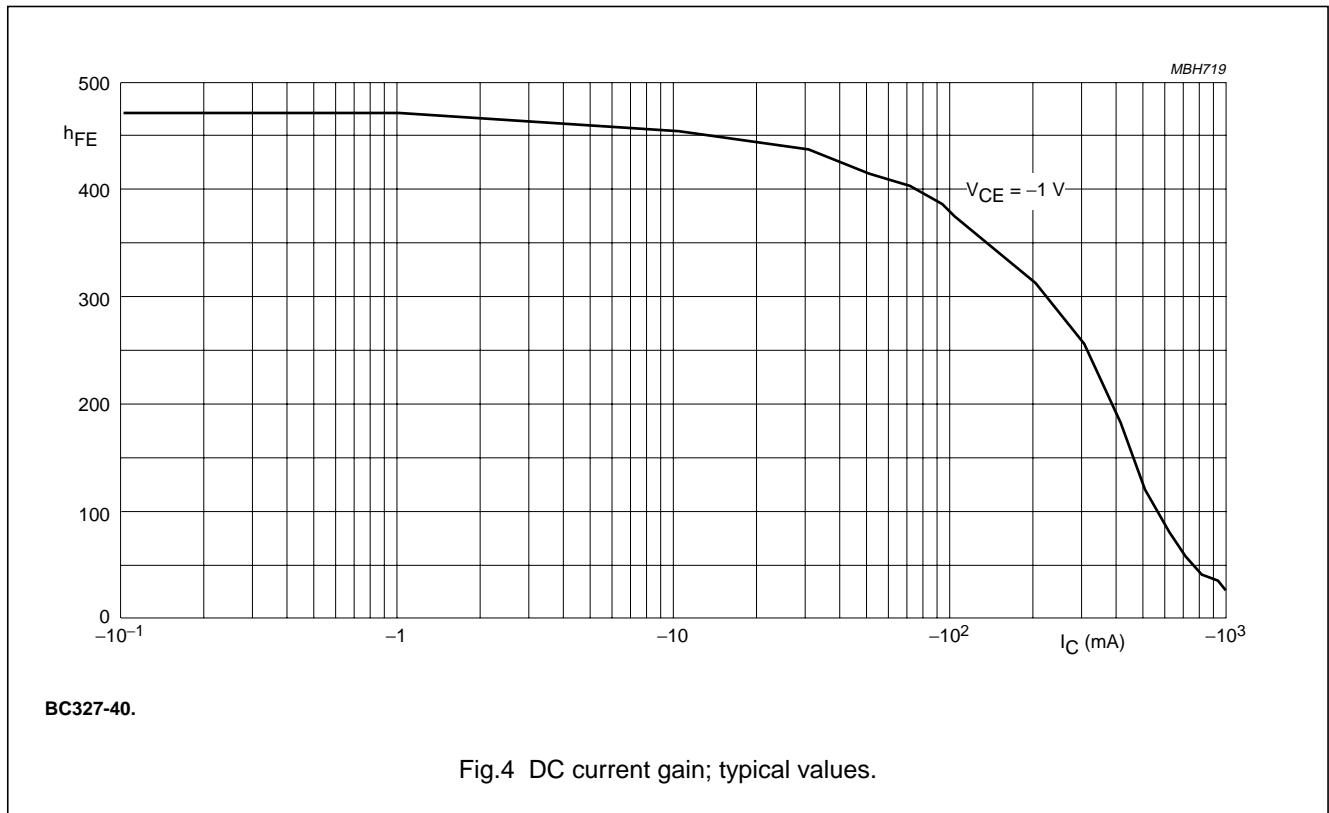
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BC327

PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



DIMENSIONS (mm are the original dimensions)

UNIT	A	b	b ₁	c	D	d	E	e	e ₁	L	L ₁ ⁽¹⁾
mm	5.2 5.0	0.48 0.40	0.66 0.56	0.45 0.40	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ		
SOT54		TO-92	SC-43		97-02-28